

## NP80N06MLG-S18-AY

### NP80N06MLG-S18-AY Information



For Reference Only

Part Number NP80N06MLG-S18-AY

Manufacturer Renesas Electronics America

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

**Description** MOSFET N-CH 60V 80A TO-220

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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## NP80N06MLG-S18-AY Specifications

Manufacturer Part Number         NP80N06MLG-S18-AY           Manufacturer         Renesas Electronics America           Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-220-3           Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         60V           Current - Continuous Drain (Id) @ 25°C         80A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         4.5V, 10V           Vgs(th) (Max) @ Id         2.5V @ 250µA           Gate Charge (Qg) (Max) @ Vgs         128nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         6900pF @ 25V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         1.8W (Ta), 115W (Tc)           Rds On (Max) @ Id, Vgs         8.6 mOhm @ 40A, 10V           Operating Temperature         175°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-220-3           Package / Case         TO-220-3           Report errors?		
Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-220-3           Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         60V           Current - Continuous Drain (Id) @ 25°C         80A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         4.5V, 10V           Vgs(th) (Max) @ Id         2.5V @ 250μA           Gate Charge (Qg) (Max) @ Vgs         128nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         6900pF @ 25V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         1.8W (Ta), 115W (Tc)           Rds On (Max) @ Id, Vgs         8.6 mOhm @ 40A, 10V           Operating Temperature         175°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-220-3           Package / Case         TO-220-3	Manufacturer Part Number	NP80N06MLG-S18-AY
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Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         60V           Current - Continuous Drain (Id) @ 25°C         80A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         4.5V, 10V           Vgs(th) (Max) @ Id         2.5V @ 250µA           Gate Charge (Qg) (Max) @ Vgs         128nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         6900pF @ 25V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         1.8W (Ta), 115W (Tc)           Rds On (Max) @ Id, Vgs         8.6 mOhm @ 40A, 10V           Operating Temperature         175°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-220-3           Package / Case         TO-220-3		Transistors - FETs, MOSFETs - Single
FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 60V Current - Continuous Drain (Id) @ 25°C 80A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2.5V @ 250µA Gate Charge (Qg) (Max) @ Vgs 128nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 6900pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 1.8W (Ta), 115W (Tc) Rds On (Max) @ Id, Vgs 8.6 mOhm @ 40A, 10V Operating Temperature 175°C (TJ) Mounting Type Through Hole Supplier Device Package 70-220-3 Package / Case 170-220-3	Package	TO-220-3
Technology  Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  80A (Tc)  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  128nC @ 10V  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  - Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Nogerating Temperature  175°C (TJ)  Mounting Type  Supplier Device Package  Package / Case  MOSFET (Metal Oxide)  60V  80A  1.80  4.5V  80A (Tc)  80A (Tc)  80A (Tc)  80A  4.5V  80A  1.8V	Series	-
Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C80A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2.5V @ 250μAGate Charge (Qg) (Max) @ Vgs128nC @ 10VInput Capacitance (Ciss) (Max) @ Vds6900pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)1.8W (Ta), 115W (Tc)Rds On (Max) @ Id, Vgs8.6 mOhm @ 40A, 10VOperating Temperature175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Cate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  8.6 mOhm @ 40A, 10V  Operating Temperature  Nounting Type  Through Hole  Supplier Device Package  Package / Case  80A (Tc)  8	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Cate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Rds On (Max) @ Id, Vgs  Noperating Temperature  Through Hole  Supplier Device Package  Package / Case  A 2.5V @ 250μA  1.28nC @ 10V  6900pF @ 25V  ±20V  FET Feature  -  Rds On (Fig. 115W (Tc)  8.6 mOhm @ 40A, 10V  Through Hole  To-220-3	Drain to Source Voltage (Vdss)	60V
Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  6900pF @ 25V  Vgs (Max)  ±20V  FET Feature  - Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  8.6 mOhm @ 40A, 10V  Operating Temperature  175°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-220-3  Package / Case  TO-220-3	Current - Continuous Drain (Id) @ 25°C	80A (Tc)
Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  6900pF @ 25V  Vgs (Max)  ±20V  FET Feature  - Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  8.6 mOhm @ 40A, 10V  Operating Temperature  175°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-220-3  Package / Case  TO-220-3	Drive Voltage (Max Rds On, Min Rds On)	4.5V, 10V
Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  E20V  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Noperating Temperature  175°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-220-3  Package / Case  TO-220-3	Vgs(th) (Max) @ Id	2.5V @ 250μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)1.8W (Ta), 115W (Tc)Rds On (Max) @ Id, Vgs8.6 mOhm @ 40A, 10VOperating Temperature175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3	Gate Charge (Qg) (Max) @ Vgs	128nC @ 10V
FET Feature - Power Dissipation (Max) 1.8W (Ta), 115W (Tc) Rds On (Max) @ Id, Vgs 8.6 mOhm @ 40A, 10V Operating Temperature 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3	Input Capacitance (Ciss) (Max) @ Vds	6900pF @ 25V
Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  8.6 mOhm @ 40A, 10V  Operating Temperature  175°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-220-3  Package / Case  TO-220-3	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs8.6 mOhm @ 40A, 10VOperating Temperature175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3	FET Feature	-
Operating Temperature 175°C (TJ)  Mounting Type Through Hole  Supplier Device Package TO-220-3  Package / Case TO-220-3	Power Dissipation (Max)	1.8W (Ta), 115W (Tc)
Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3	Rds On (Max) @ Id, Vgs	8.6 mOhm @ 40A, 10V
Supplier Device Package TO-220-3 Package / Case TO-220-3	Operating Temperature	175°C (TJ)
Package / Case TO-220-3	Mounting Type	Through Hole
	Supplier Device Package	TO-220-3
Report errors?	Package / Case	TO-220-3
		Report errors?

#### NP80N06MLG-S18-AY Guarantees



#### **Ouality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

### NP80N06MLG-S18-AY Payment Methods



















### NP80N06MLG-S18-AY Shipping Methods













If you have any question about NP80N06MLG-S18-AY, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com